

Super Junction Power MOSFET

PRODUCT SUMMARY		
V _{DS} (V) at T _J max.	900	
R _{DS(on)} typ. (Ω) at 25 °C	V _{GS} = 10 V	0.27
Q _g max. (nC)	122	
Q _{gs} (nC)	14	
Q _{gd} (nC)	23	
Configuration	Single	

FEATURES

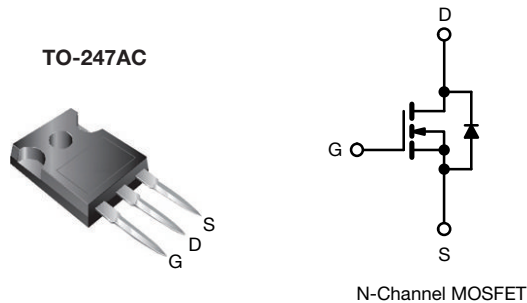
- Low figure-of-merit (FOM) R_{on} x Q_g
- Low input capacitance (C_{iss})
- Reduced switching and conduction losses
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Industrial
 - Welding
 - Induction heating
 - Motor drives
 - Battery chargers
 - Renewable energy
 - Solar (PV inverters)




ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-source voltage	V _{DS}	900	V
Gate-source voltage	V _{GS}	± 30	
Continuous drain current (T _J = 150 °C)	V _{GS} at 10 V	T _C = 25 °C	A
		T _C = 100 °C	
Pulsed drain current ^a	I _{DM}	60	
Linear derating factor		1.7	W/°C
Single pulse avalanche energy ^b	E _{AS}	383	mJ
Maximum power dissipation	P _D	218	W
Operating junction and storage temperature range	T _J , T _{stg}	-55 to +150	°C
Drain-source voltage slope	dV/dt	T _J = 125 °C	V/ns
Reverse diode dV/dt ^d			
Soldering recommendations (peak temperature) ^c	For 10 s	300	°C

Notes

- Repetitive rating; pulse width limited by maximum junction temperature
- V_{DD} = 140 V, starting T_J = 25 °C, L = 28.2 mH, R_g = 25 Ω, I_{AS} = 5.0 A
- 1.6 mm from case
- I_{SD} ≤ I_D, dI/dt = 100 A/μs, starting T_J = 25 °C

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R_{thJA}	-	62	°C/W
Maximum junction-to-case (drain)	R_{thJC}	-	0.6	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		900	-	-	V
V_{DS} temperature coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$		-	1.08	-	V/°C
Gate-source threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-source leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$		-	-	± 1	μA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$		-	-	1	μA
		$V_{DS} = 640\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	10	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 8.5\text{ A}$	-	0.27	-	Ω
Forward transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 8.5\text{ A}$		-	8.7	-	S
Dynamic							
Input capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$		-	2408	-	pF
Output capacitance	C_{oss}			-	81	-	
Reverse transfer capacitance	C_{rss}			-	9	-	
Effective output capacitance, energy related ^a	$C_{o(er)}$			-	58	-	
Effective output capacitance, time related ^b	$C_{o(tr)}$	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$		-	296	-	
Total gate charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8.5\text{ A}, V_{DS} = 480\text{ V}$	-	61	122	nC
Gate-source charge	Q_{gs}			-	14	-	
Gate-drain charge	Q_{gd}			-	23	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 480\text{ V}, I_D = 8.5\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$		-	22	44	ns
Rise time	t_r			-	24	48	
Turn-off delay time	$t_{d(off)}$			-	71	142	
Fall time	t_f			-	26	52	
Gate input resistance	R_g			$f = 1\text{ MHz}, \text{open drain}$		0.3	
Drain-Source Body Diode Characteristics							
Continuous source-drain diode current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	15	A
Pulsed diode forward current	I_{SM}			-	-	45	
Diode forward voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8.5\text{ A}, V_{GS} = 0\text{ V}$		-	-	1.2	V
Reverse recovery time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 8.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 25\text{ V}$		-	416	832	ns
Reverse recovery charge	Q_{rr}			-	6.4	12.8	μC
Reverse recovery current	I_{RRM}			-	27	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS}

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

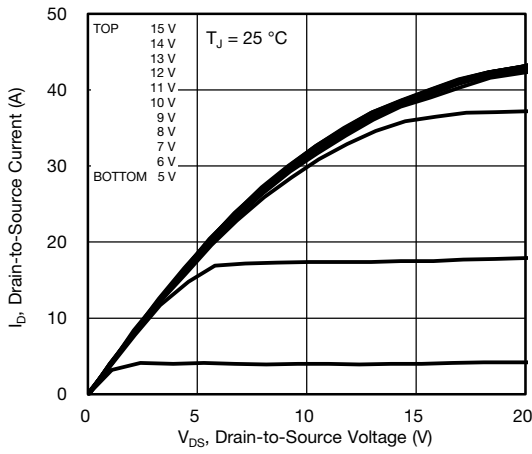


Fig. 1 - Typical Output Characteristics

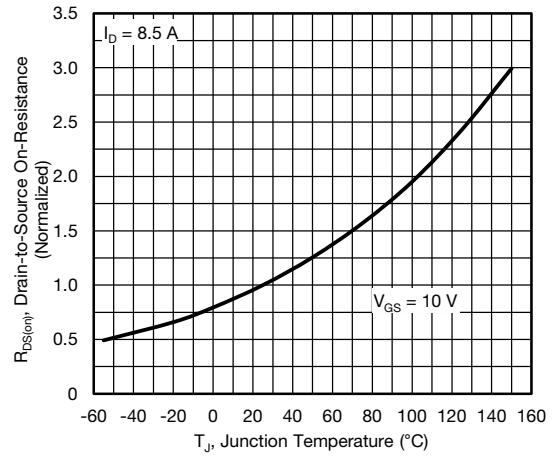


Fig. 4 - Normalized On-Resistance vs. Temperature

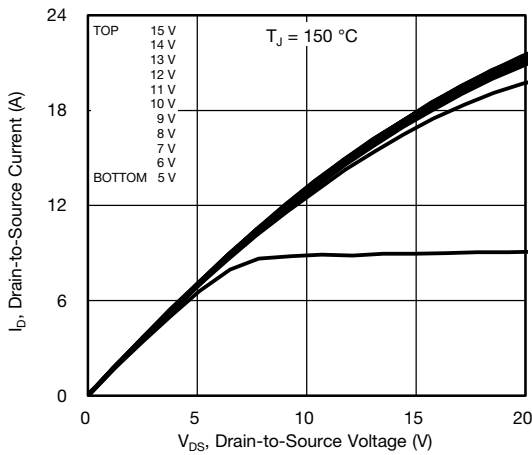


Fig. 2 - Typical Output Characteristics

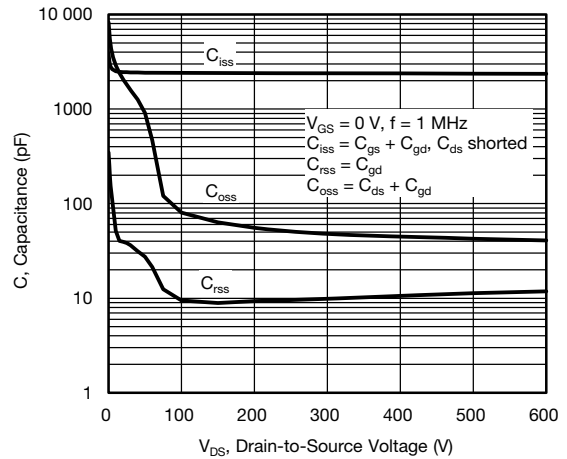


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

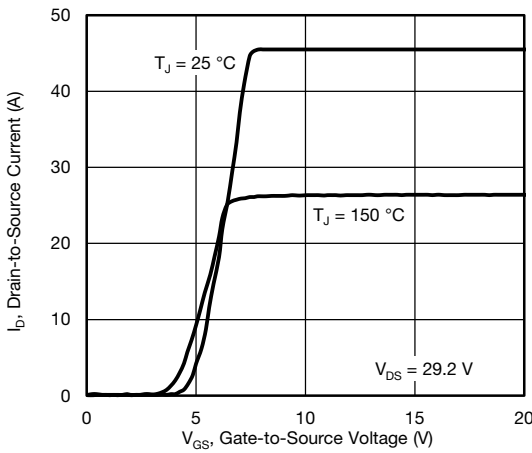


Fig. 3 - Typical Transfer Characteristics

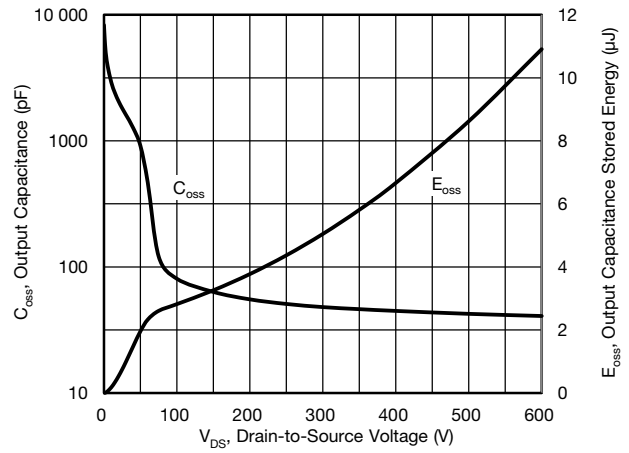


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

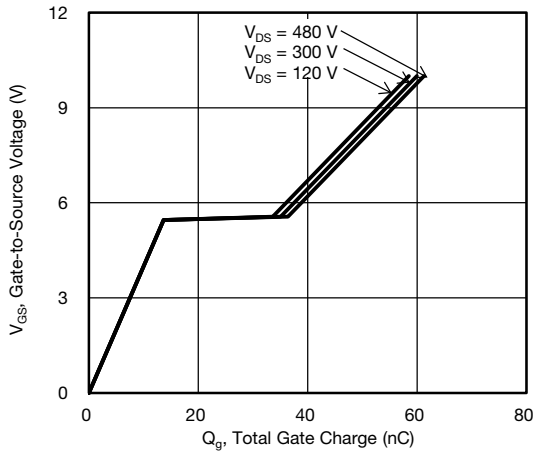


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

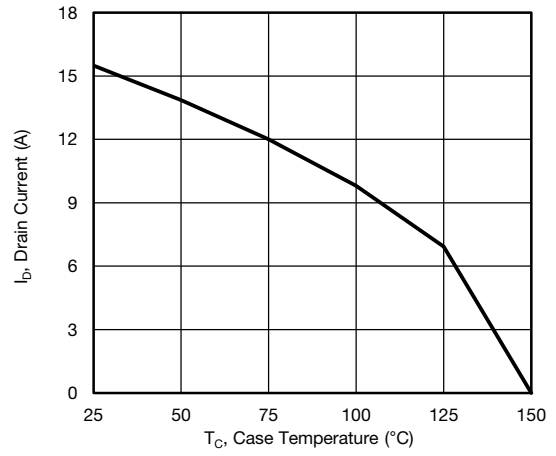


Fig. 10 - Maximum Drain Current vs. Case Temperature

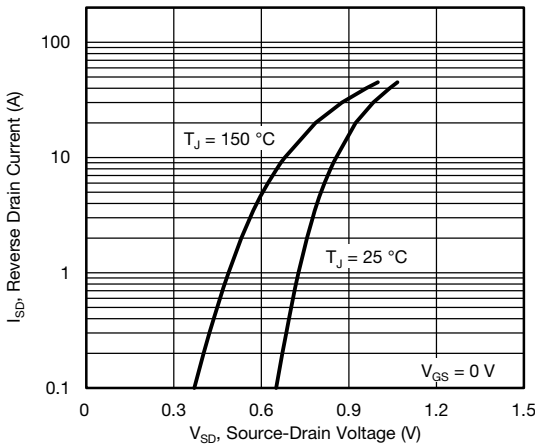


Fig. 8 - Typical Source-Drain Diode Forward Voltage

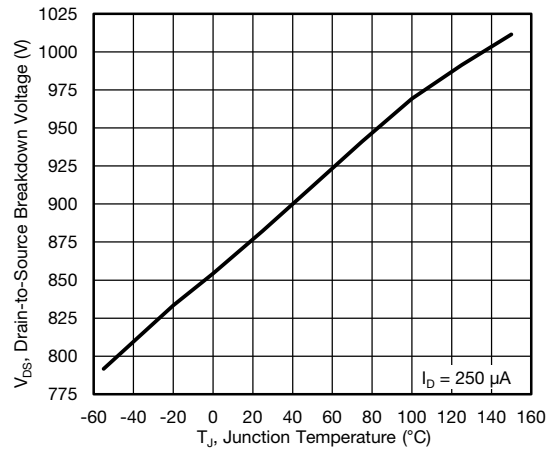


Fig. 11 - Temperature vs. Drain-to-Source Voltage

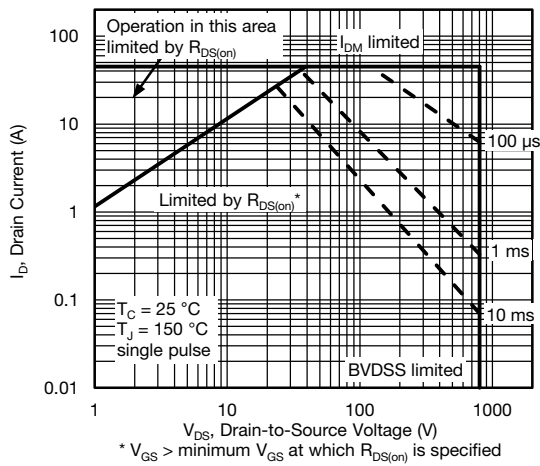


Fig. 9 - Maximum Safe Operating Area

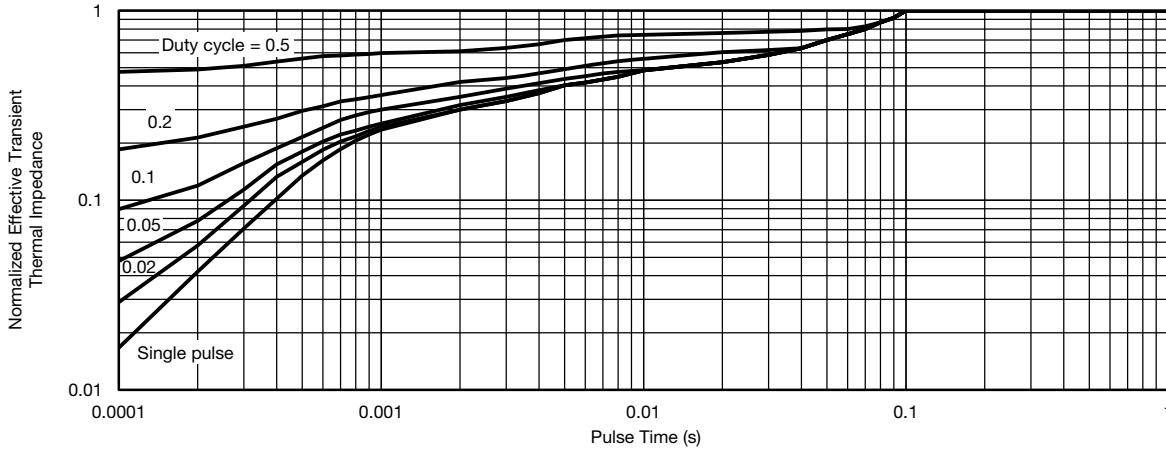


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

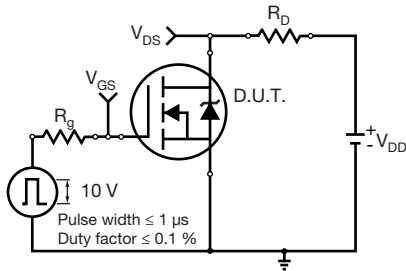


Fig. 13 - Switching Time Test Circuit

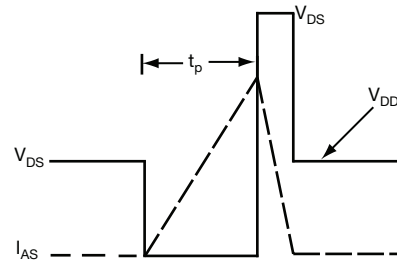


Fig. 16 - Unclamped Inductive Waveforms

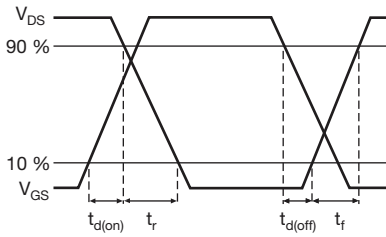


Fig. 14 - Switching Time Waveforms

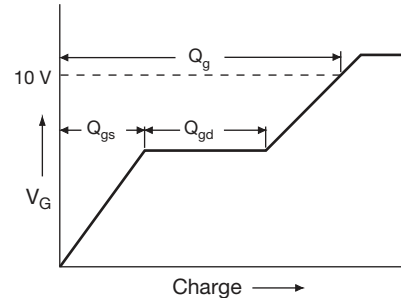


Fig. 17 - Basic Gate Charge Waveform

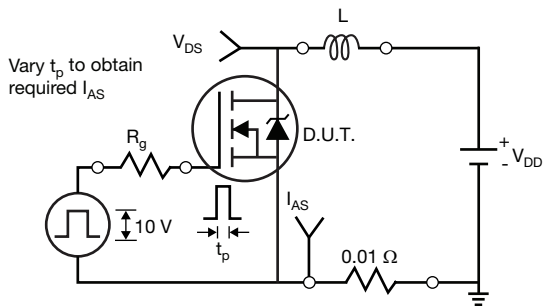


Fig. 15 - Unclamped Inductive Test Circuit

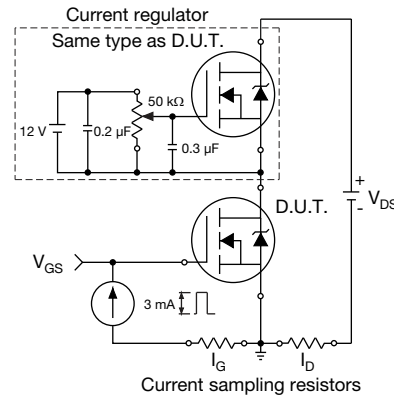


Fig. 18 - Gate Charge Test Circuit

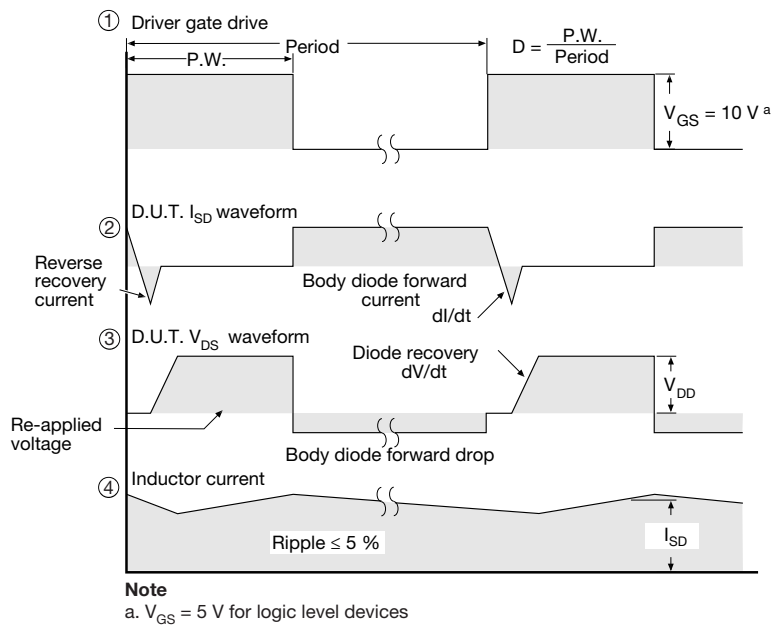
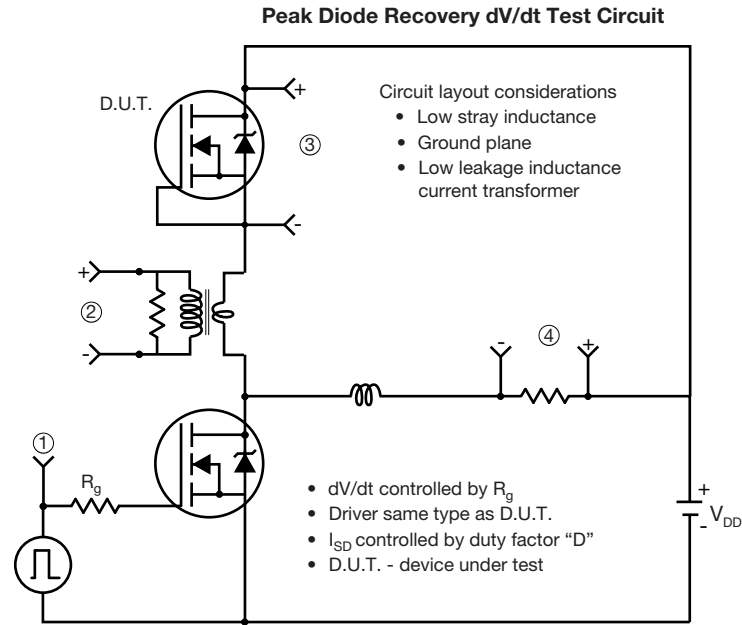


Fig. 19 - For N-Channel

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